

STANDARD RECOVERY DIODES

- **Junction Size:** Rectangular 207 x 157 mils
- **Wafer Size:** 4"
- **V_{RRM} Class:** 800 and 1200 V
- **Passivation Process:** Glassivated MOAT
- **Reference IR Packaged Part:** 20ETS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	1100mV	T _J = Amb., I _F = 20 A
V _{RRM} Reverse Breakdown Voltage Range	800 and 1200 V	T _J = Amb., I _{RRM} = 100 μA (1)

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	207 x 157 mils (see drawing)
Wafer Diameter	100mm, with std. < 110 > flat
Wafer Thickness	300 μm
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR207DM..CCB Series

Bulletin I0139J 01/00

International
IR Rectifier

Ordering Information Table

Device Code						
IR	207	D	M	12	C	CB
①	②	③	④	⑤	⑥	⑦

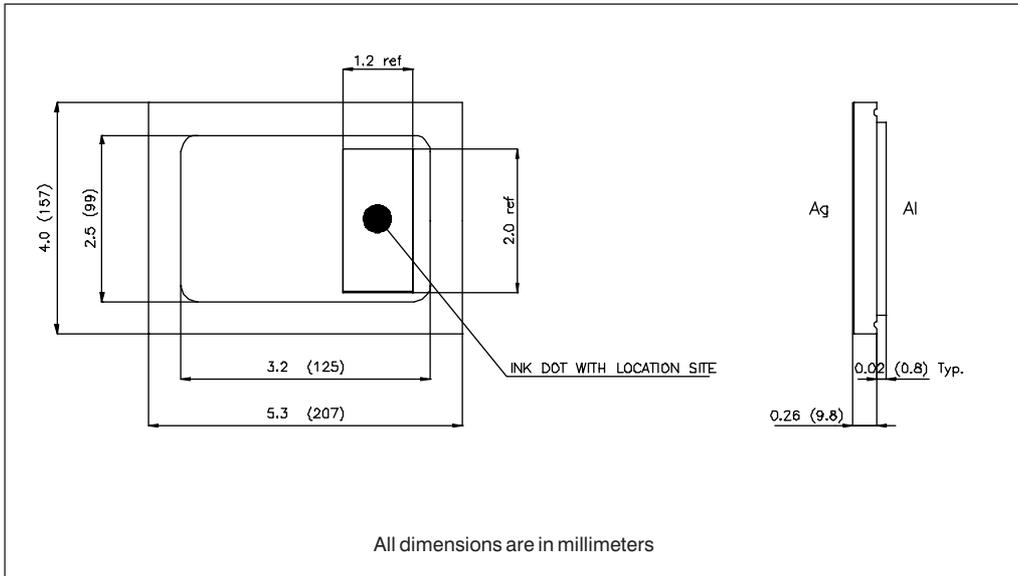
- 1** - International Rectifier Device
- 2** - Chip Dimension in Mils
- 3** - Type of Device: D = Wire Bondable Standard Recovery Diode
- 4** - Passivation Process: M = Glassivated MOAT
- 5** - Voltage code: Code x 100 = V_{RRM}
- 6** - Metallization: C = Aluminium (Anode) - Silver (Cathode)
- 7** - CB = Probed Uncut Die (wafer in box)
None = Probed Die in chip carrier

Available Class

08 = 800 V

12 = 1200 V

Outline Table



Wafer Layout

